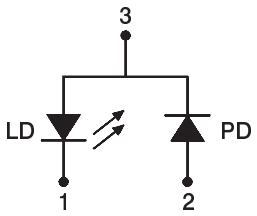
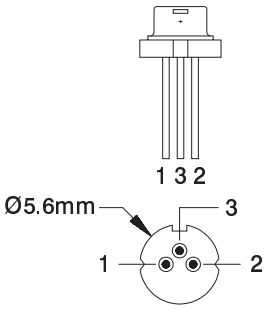
Sony SLD1132VS
Laser Diode Specifications

The Sony SLD1132VS is a AlGaInP visible laser diode that's designed for laser pointers. The operating wavelength of 635nm is approximately seven times brighter than a typical 670nm laser diode. The diode has a quantum well structure and single longitudinal mode. The SLD1132VS has a Ø5.6mm package.



Internal Circuit



Package Type: Ø5.6mm

Absolute Maximum Ratings (Tc=25 °C)

Characteristic	Symbol	Value	Unit
Optical output power	Po	5	mW
Laser diode reverse voltage	VR(LD)	2	V
Photodiode reverse voltage	VR(PD)	15	V
Operating temperature	Topr	–10 to +40	°C
Storage temperature	Tstg	–40 to +85	°C

Operating and Electrical Characteristics (Tc=25 °C)

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Threshold current	Ith	–	50	70	mA	–
Operating current	Iop	–	60	80	mA	Po=3mW
Differential efficiency	η	0.15	0.35	0.8	mW/mA	Po=3mW
Operating voltage	Vop	–	2.4	3.0	V	Po=3mW
Lasing Wavelength	λp	625	635	645	nm	Po=3mW
Beam divergence (parallel)	θ//	5	7	12	deg	Po=3mW, (FWHM)
Beam divergence (perpendicular)	θ⊥	24	32	40	deg	Po=3mW, (FWHM)
Monitor current	Im	0.05	0.10	0.30	mA	Po=3mW, VR(PD)=5V
Astigmatism	As	–	–	20	microns	–

For current pricing and stock availability please contact:

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